

REMARKS

Favorable reconsideration of this application is requested in view of the above amendments and the following remarks. Claims 1-19 are pending. The revision to claim 1 is supported, for example, at page 13, line 34.

Claims 6-17 stand withdrawn from consideration due to restriction. Applicants reserve the option to revise the non-elected method claims to track allowable product claims and thus make the method claims suitable for reinstatement.

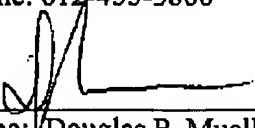
Claims 1-5 and 18-19 have been rejected as obvious over Ueta in view of Flynn. Applicants respectfully traverse this rejection. Both Ueta and Flynn provide Group III nitride crystals produced on offcut seed crystals by a vapor phase epitaxy process. There is no reasonable basis to conclude that the products of the reference would exhibit a dislocation density on the order of about $1 \times 10^2 \text{ cm}^{-2}$ or lower. As exemplified by the discussion at col. 6, lines 12-18 and col. 7, lines 31-32 of Ueta, the reference products show dislocation densities about seven orders of magnitude higher than that required by claim 1. Nothing in the art of record suggests any reason to expect that the dislocation densities could be lowered so dramatically, or provides any teaching of how this might be accomplished.

In view of the above, Applicants request reconsideration of the application in the form of a Notice of Allowance.

Respectfully submitted,

Hamre, Schumann,
Mueller & Larson, P.C.
P.O. Box 2902-0902
Minneapolis, MN 55402
Phone: 612-455-3800

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By 
Name: Douglas P. Mueller
Reg. No. 30,300
Customer No. 53148